

wherein:

said substrate is made of a non-oxide ceramic containing 0.05 to 5% by weight of oxygen; and

the pore diameter of the maximum pore thereof is 50 μm or less.

A1
end
2. (Amended) The ceramic heater for the semiconductor-producing/examining device according to claim 1,

wherein said non-oxide ceramic is a nitride ceramic.

3. (Amended) The ceramic heater for the semiconductor-producing/examining device according to claim 1,

wherein said non-oxide ceramic is a carbide ceramic.

5. (Amended) The ceramic heater for the semiconductor-producing/examining device according to claim 1,

A2
wherein said ceramic substrate has a porosity of 5% or less.

6. (Amended) The ceramic heater for the semiconductor-producing/examining device according to claim 1,

wherein said ceramic substrate is capable of use within the temperature range of 100 to 700°C.

7. (Amended) The ceramic heater for the semiconductor-producing/examining device according to claim 1,

wherein said ceramic substrate has a thickness of 25 mm or less, and a diameter of 200 mm or more.

8. (Amended) The ceramic heater for the semiconductor-producing/examining device according to claim 1,

A2
enc wherein said ceramic substrate has a plurality of through holes into which lifter pins
for a semiconductor wafer are capable of being inserted.

Please cancel Claim 4.

Please add the following new Claims 9-16 as follows:

9. (New) The ceramic heater for the semiconductor-producing/examining device
according to claim 1,

wherein the pore diameter of the maximum pore thereof is 10 μm or less.

10. (New) The ceramic heater for the semiconductor-producing/examining device
according to claim 1,

wherein said ceramic substrate contains oxygen in an amount of 0.1 to 5% by weight.

11. (New) The ceramic heater for the semiconductor-producing/examining device
according to claim 1,

wherein said ceramic substrate comprises an alkali metal oxide, an alkali earth metal
oxide, or a rare earth element oxide.

12. (New) The ceramic heater for the semiconductor-producing/examining device
according to claim 1,

wherein an electrostatic electrode or an RF electrode is embedded inside the ceramic
substrate.

13. (New) The ceramic heater for the semiconductor-producing/examining device
according to claim 1,

wherein said heating element is a Peltier device.

14. (New) The ceramic heater for the semiconductor-producing/examining device
according to claim 1,

wherein said heating element is selected from the group consisting of a conductive ceramic, a metal foil, a metal sintered body, and a metal wire.

15. (New) The ceramic heater for the semiconductor-producing/examining device according to claim 1,

wherein a chuck top conductor layer is formed on the surface of said ceramic substrate.

16. (New) The ceramic heater for the semiconductor-producing/examining device according to claim 1,

wherein said ceramic substrate contains BN.

DISCUSSION OF THE AMENDMENT

Claim 1 has been amended as supported in the specification at page 6, lines 28-30 and page 11, lines 1-4. Claim 4 has been canceled as redundant. Claims 2, 3 and 5-8 have been amended to be consistent with the amendment to Claim 1. In addition, Claims 5-8 have been amended to depend on Claim 1 only. Claims 6 and 8 have been further amended to recite a capability of the ceramic heater, in place of an intended use.

New Claims 9-16 have been added. Claim 9 is supported in the specification at page 6, lines 13-14. Claim 10 is supported at page 6, lines 28-30. Claim 11 is supported at page 9, lines 7-8. Claim 12 is supported at page 11, lines 4-8. Claim 13 is supported at page 16, lines 29-30, and Fig. 6. Claim 14 is supported at page 17, lines 8-10. Claim 15 is supported at page 11, lines 8-12. Finally, Claim 16 is supported at page 6, lines 18-19.

No new matter has been added by the above amendment. Claims 1-3 and 5-16 are now pending in the application.